



NCE N-Channel Enhancement Mode Power MOSFET

Description

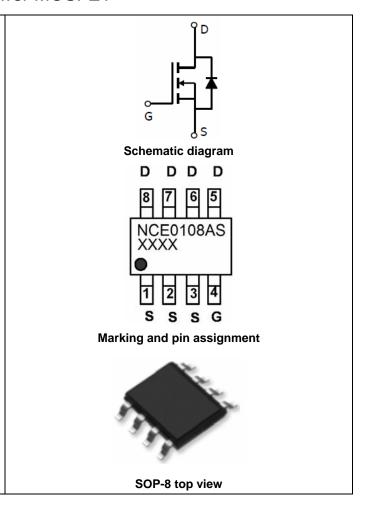
The NCE0108AS uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

- V_{DS} = 100V, I_D =8A $R_{DS(ON)}$ < 28m Ω @ V_{GS} =10V (Typ:22m Ω)
- Special process technology for high ESD capability
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current

Application

- DC/DC Primary Side Switch
- Telecom/Server
- Synchronous Rectification



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE0108AS	NCE0108AS	SOP-8	Ø330mm	12mm	2500 units

Absolute Maximum Ratings (T_A=25 ℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	100	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	I _D	8	А
Drain Current-Continuous(T _C =100 °C)	I _D (100℃)	5.6	А
Pulsed Drain Current	I _{DM}	57	Α
Maximum Power Dissipation	P _D	2.6	W
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 To 150	$^{\circ}\!\mathbb{C}$

Thermal Characteristic

_				
	Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ hetaJA}$	48	°C/W



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Electrical Characteristics (T_A=25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	100	110	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	1.3	1.8	2.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =8A	-	22	28	mΩ
Forward Transconductance	g FS	V _{DS} =5V,I _D =8A	20	-	-	S
Dynamic Characteristics (Note4)	•					
Input Capacitance	C _{lss}	\/ -50\/\/ -0\/	-	2000	-	PF
Output Capacitance	Coss	V_{DS} =50V, V_{GS} =0V, F=1.0MHz	-	300	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.UIVID2	-	250	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	12	-	nS
Turn-on Rise Time	t _r	V_{DD} =50 V , I_D =10 A , R_L =5 Ω ,	-	10	-	nS
Turn-Off Delay Time	$t_{d(off)}$	$R_G=1\Omega,V_{GS}=10V$	-	19	-	nS
Turn-Off Fall Time	t _f		-	8	-	nS
Total Gate Charge	Q_g		-	42	-	nC
Gate-Source Charge	Q_{gs}	I _D =10A,V _{DD} =50V,V _{GS} =10V	-	9	-	nC
Gate-Drain Charge	Q_{gd}		-	10	-	nC
Drain-Source Diode Characteristics	•					
Diode Forward Voltage (Note 3)	V_{SD}	V _{GS} =0V,I _S =8A	-	0.85	1.2	V
Diode Forward Current (Note 2)	Is		-	-	8	Α
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = 8A	-	30		nS
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)}$	-	44		nC

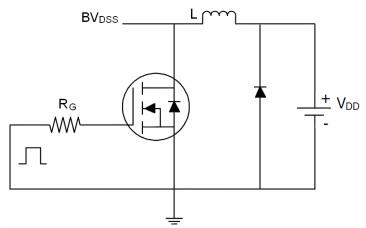
Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- **3.** Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production

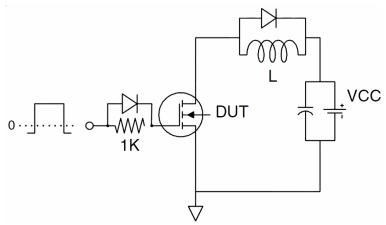


Test Circuit

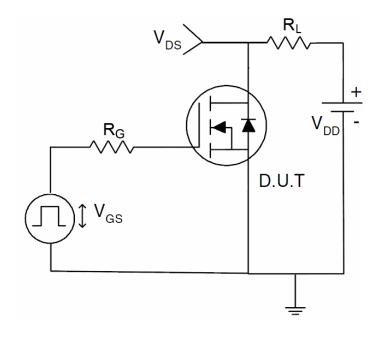
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit





Typical Electrical and Thermal Characteristics (Curves)

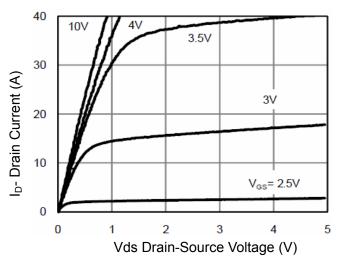


Figure 1 Output Characteristics

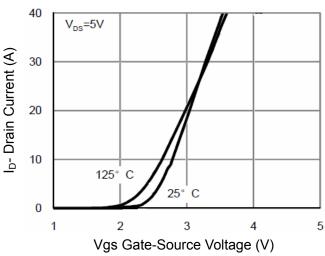


Figure 2 Transfer Characteristics

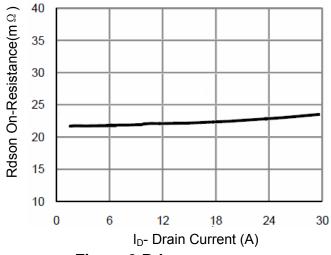


Figure 3 Rdson- Drain Current

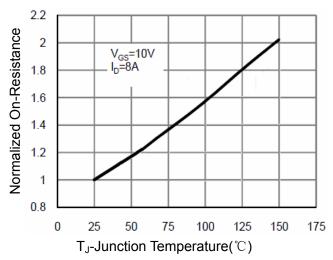
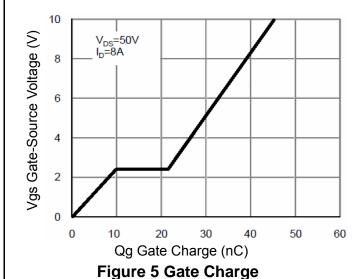
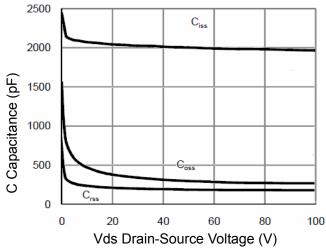


Figure 4 Rdson-JunctionTemperature



1.0E+02 1.0E+01 Reverse Drain Current 1.0E+00 125° C 1.0E-01 1.0E-02 25° C 1.0E-03 1.0E-04 _<u>ω</u> 1.0E-05 0.2 0.4 0.6 8.0 1.0 1.2 Vsd Source-Drain Voltage (V)

Figure 6 Source- Drain Diode Forward



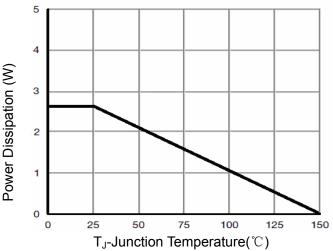
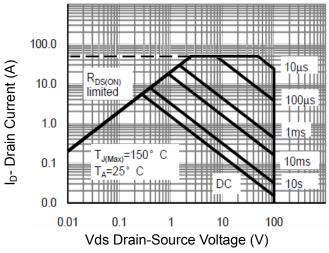


Figure 7 Capacitance vs Vds





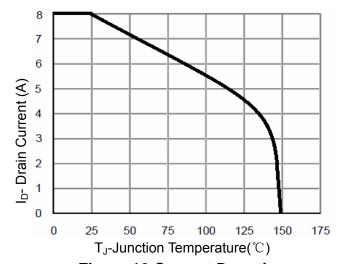
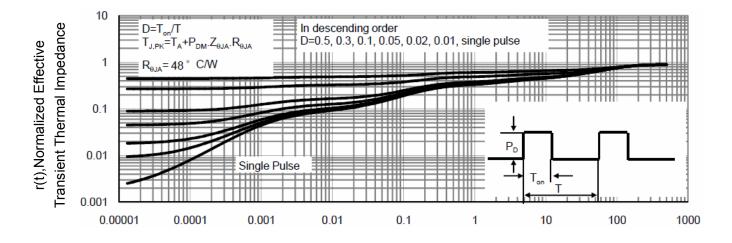


Figure 8 Safe Operation Area

Figure 10 Current De-rating



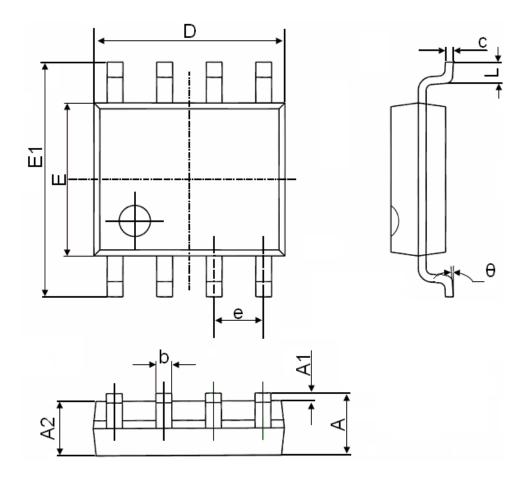
Square Wave Pluse Duration(sec)

Figure 11 Normalized Maximum Transient Thermal Impedance





SOP-8 Package Information



Symbol	Dimensions I	n Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	1.350	1.750	0.053	0.069	
A1	0.100	0.250	0.004	0.010	
A2	1.350	1.550	0.053	0.061	
b	0.330	0.510	0.013	0.020	
С	0.170	0.250	0.006	0.010	
D	4.700	5.100	0.185	0.200	
E	3.800	4.000	0.150	0.157	
E1	5.800	6.200	0.228	0.244	
е	1.270	(BSC)	0.050	(BSC)	
L	0.400	1.270	0.016	0.050	
θ	0°	8°	0°	8°	



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